

NUD3112

Integrated Relay, Inductive Load Driver

This device is used to switch inductive loads such as relays, solenoids incandescent lamps, and small DC motors without the need of a free-wheeling diode. The device integrates all necessary items such as the MOSFET switch, ESD protection, and Zener clamps. It accepts logic level inputs thus allowing it to be driven by a large variety of devices including logic gates, inverters, and microcontrollers.

Features

- Provides a Robust Driver Interface Between D.C. Relay Coil and Sensitive Logic Circuits
- Optimized to Switch Relays of 12 V Rail
- Capable of Driving Relay Coils Rated up to 6.0 W at 12 V
- Internal Zener Eliminates the Need of Free-Wheeling Diode
- Internal Zener Clamp Routes Induced Current to Ground for Quieter Systems Operation
- Low $V_{DS(ON)}$ Reduces System Current Drain
- SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These are Pb-Free Devices

Typical Applications

- Telecom: Line Cards, Modems, Answering Machines, FAX
- Computers and Office: Photocopiers, Printers, Desktop Computers
- Consumer: TVs and VCRs, Stereo Receivers, CD Players, Cassette Recorders
- Industrial: Small Appliances, Security Systems, Automated Test Equipment, Garage Door Openers



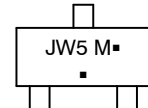
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MARKING DIAGRAMS



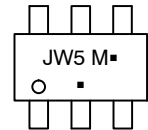
**SOT-23
CASE 318
STYLE 21**



JW5 = Specific Device Code
M = Date Code
▪ = Pb-Free Package
(Note: Microdot may be in either location)



**SC-74
CASE 318F
STYLE 7**



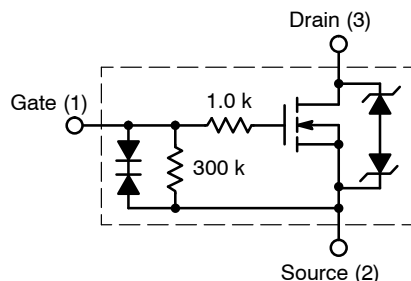
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ORDERING INFORMATION

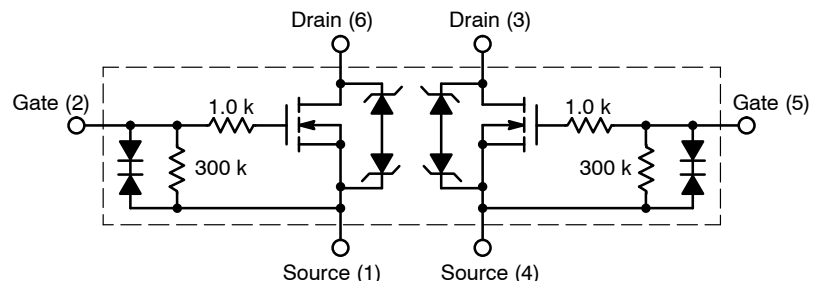
Device	Package	Shipping†
NUD3112LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
SZNUD3112LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
NUD3112DMT1G	SC-74 (Pb-Free)	3000 / Tape & Reel
SZNUD3112DMT1G	SC-74 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

INTERNAL CIRCUIT DIAGRAMS



CASE 318



CASE 318F

NUD3112

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Rating	Value	Unit	
V_{DSS}	Drain to Source Voltage – Continuous	14	V_{dc}	
V_{GS}	Gate to Source Voltage – Continuous	6	V_{dc}	
I_D	Drain Current – Continuous	500	mA	
E_z	Single Pulse Drain-to-Source Avalanche Energy ($T_{Jinitial} = 25^\circ\text{C}$)	50	mJ	
T_J	Junction Temperature	150	$^\circ\text{C}$	
T_A	Operating Ambient Temperature	-40 to 85	$^\circ\text{C}$	
T_{stg}	Storage Temperature Range	-65 to +150	$^\circ\text{C}$	
P_D	Total Power Dissipation (Note 1) Derating Above 25°C	SOT-23	225	mW
			1.8	$\text{mW}/^\circ\text{C}$
P_D	Total Power Dissipation (Note 1) Derating Above 25°C	SC-74	380	mW
			3.0	$\text{mW}/^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance Junction-to-Ambient (Note 1)	SOT-23	556	$^\circ\text{C}/\text{W}$
		SC-74	329	
ESD	Human Body Model (HBM) According to EIA/JESD22/A114	2000	V	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Mounted onto minimum pad board.

TYPICAL ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Characteristic	Min	Typ	Max	Unit
--------	----------------	-----	-----	-----	------

OFF CHARACTERISTICS

V_{BRDSS}	Drain to Source Sustaining Voltage (Internally Clamped) ($I_D = 10\text{ mA}$)	14	16	17	V
B_{VGS0}	$I_g = 1.0\text{ mA}$	-	-	8	V
I_{DSS}	Drain to Source Leakage Current ($V_{DS} = 12\text{ V}$, $V_{GS} = 0\text{ V}$, $T_A = 25^\circ\text{C}$) ($V_{DS} = 12\text{ V}$, $V_{GS} = 0\text{ V}$, $T_A = 85^\circ\text{C}$)	-	-	20	μA
		-	-	40	
I_{GSS}	Gate Body Leakage Current ($V_{GS} = 3.0\text{ V}$, $V_{DS} = 0\text{ V}$) ($V_{GS} = 5.0\text{ V}$, $V_{DS} = 0\text{ V}$)	-	-	35	μA
		-	-	65	

ON CHARACTERISTICS

$V_{GS(th)}$	Gate Threshold Voltage ($V_{GS} = V_{DS}$, $I_D = 1.0\text{ mA}$) ($V_{GS} = V_{DS}$, $I_D = 1.0\text{ mA}$, $T_A = 85^\circ\text{C}$)	0.8 0.8	1.2 -	1.4 1.4	V
$R_{DS(on)}$	Drain to Source On-Resistance ($I_D = 250\text{ mA}$, $V_{GS} = 3.0\text{ V}$) ($I_D = 500\text{ mA}$, $V_{GS} = 3.0\text{ V}$) ($I_D = 500\text{ mA}$, $V_{GS} = 5.0\text{ V}$) ($I_D = 500\text{ mA}$, $V_{GS} = 3.0\text{ V}$, $T_A = 85^\circ\text{C}$) ($I_D = 500\text{ mA}$, $V_{GS} = 5.0\text{ V}$, $T_A = 85^\circ\text{C}$)	-	-	1.2	Ω
		-	-	1.3	
		-	-	0.9	
		-	-	1.3	
		-	-	0.9	
$I_{DS(on)}$	Output Continuous Current ($V_{DS} = 0.25\text{ V}$, $V_{GS} = 3.0\text{ V}$) ($V_{DS} = 0.25\text{ V}$, $V_{GS} = 3.0\text{ V}$, $T_A = 85^\circ\text{C}$)	300	400	-	mA
		200	-	-	
g_{FS}	Forward Transconductance ($V_{OUT} = 12.0\text{ V}$, $I_{OUT} = 0.25\text{ A}$)	350	490	-	mmhos

NUD3112

TYPICAL ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Characteristic	Min	Typ	Max	Unit
DYNAMIC CHARACTERISTICS					
C_{iss}	Input Capacitance ($V_{DS} = 12\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 10\text{ kHz}$)	-	23	-	pF
C_{oss}	Output Capacitance ($V_{DS} = 12\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 10\text{ kHz}$)	-	30	-	pF
C_{rss}	Transfer Capacitance ($V_{DS} = 12.0\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 10\text{ kHz}$)	-	7	-	pF

SWITCHING CHARACTERISTICS

Symbol	Characteristic	Min	Typ	Max	Units
t_{PHL} t_{PLH}	Propagation Delay Times: High to Low Propagation Delay; Figure 1 ($V_{DS} = 12\text{ V}$, $V_{GS} = 5.0\text{ V}$) Low to High Propagation Delay; Figure 1 ($V_{DS} = 12\text{ V}$, $V_{GS} = 5.0\text{ V}$)	- -	21 91	- -	nS
t_f t_r	Transition Times: Fall Time; Figure 1 ($V_{DS} = 12\text{ V}$, $V_{GS} = 5.0\text{ V}$) Rise Time; Figure 1 ($V_{DS} = 12\text{ V}$, $V_{GS} = 5.0\text{ V}$)	- -	36 61	- -	nS

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

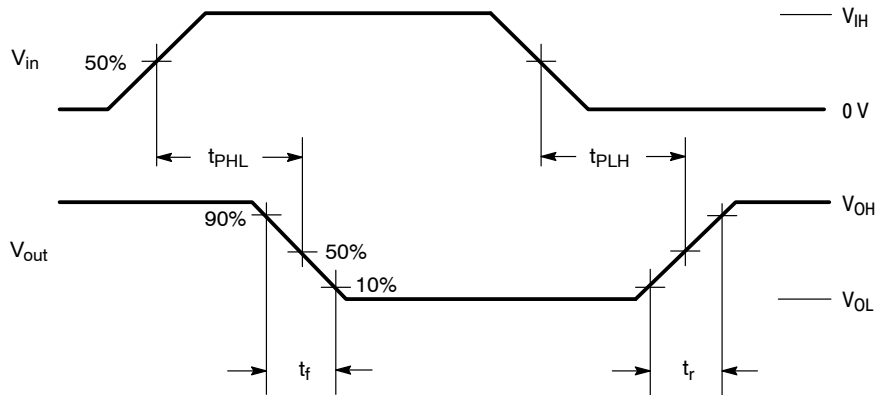


Figure 1. Switching Waveforms

NUD3112

TYPICAL PERFORMANCE CURVES ($T_J = 25^\circ\text{C}$ unless otherwise specified)

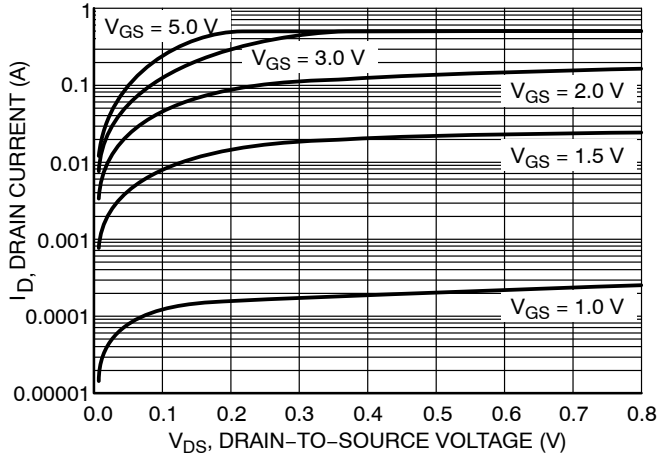


Figure 2. Output Characteristics

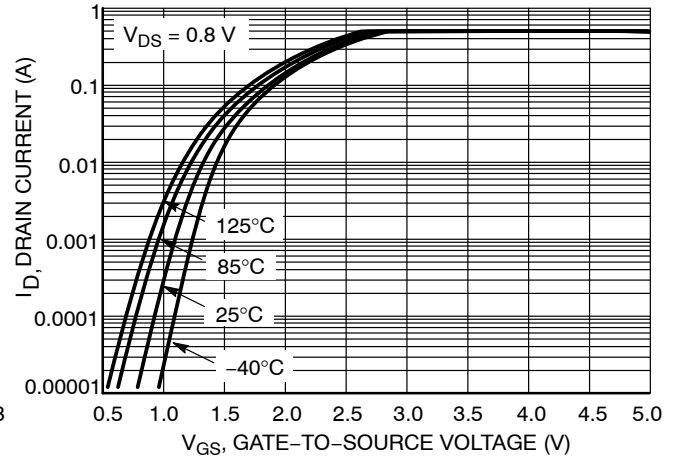


Figure 3. Transfer Function

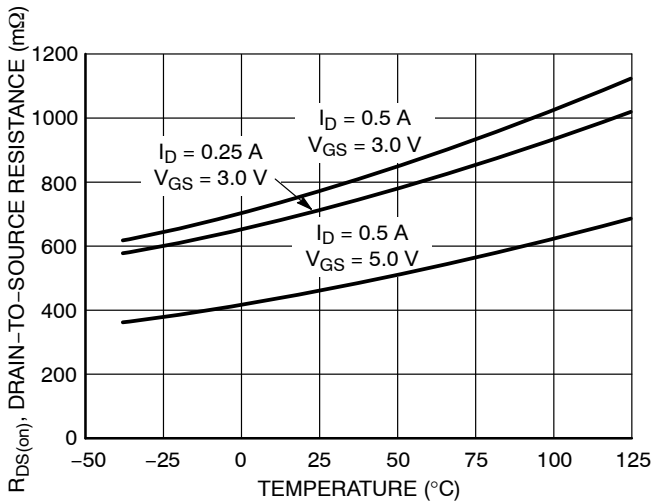


Figure 4. On-Resistance Variation vs. Temperature

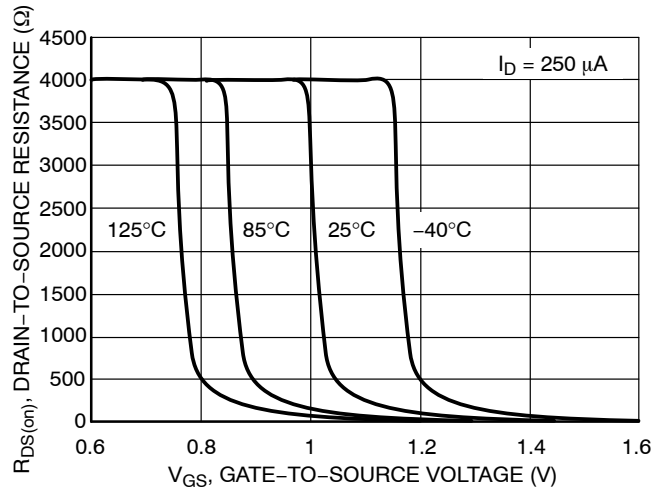


Figure 5. $R_{DS(ON)}$ Variation vs. Gate-to-Source Voltage

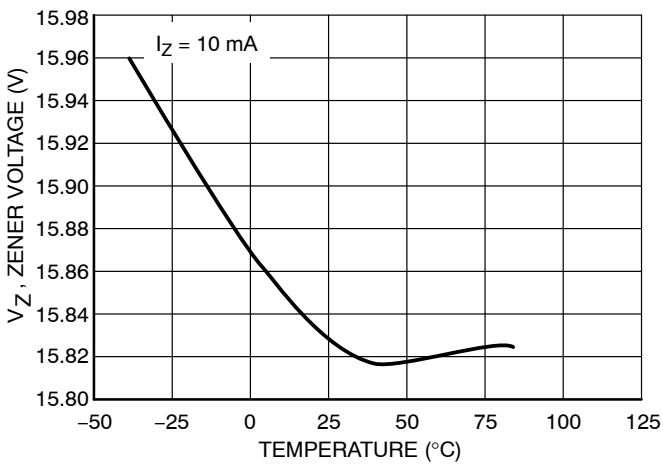


Figure 6. Zener Voltage vs. Temperature

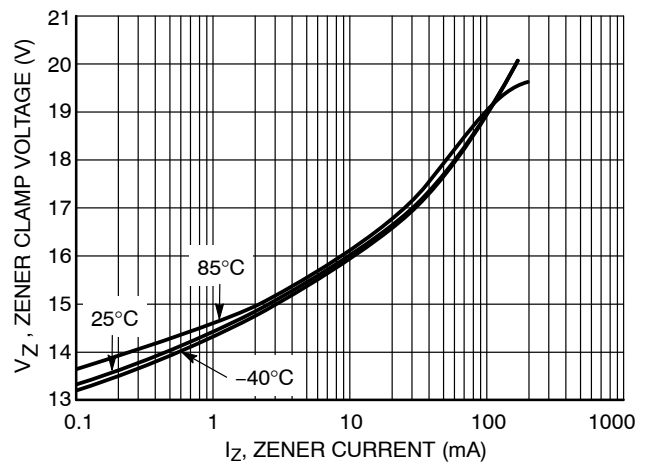


Figure 7. Zener Clamp Voltage vs. Zener Current

NUD3112

TYPICAL PERFORMANCE CURVES ($T_J = 25^\circ\text{C}$ unless otherwise specified)

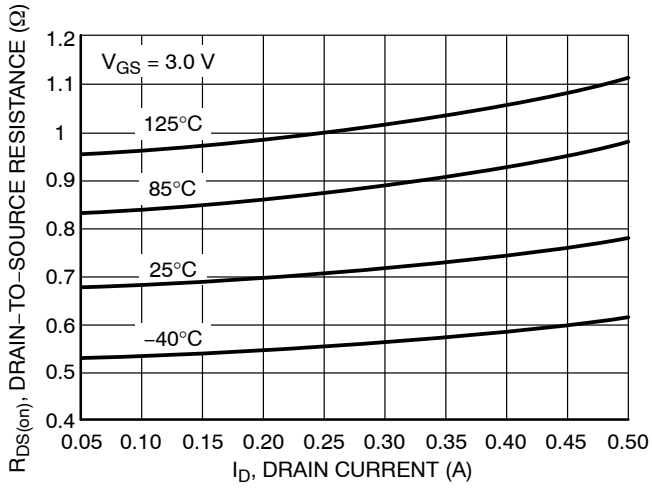


Figure 8. On-Resistance vs. Drain Current and Temperature

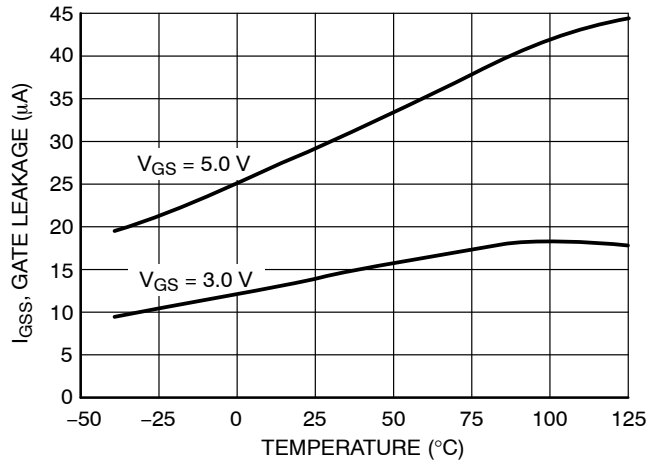


Figure 9. Gate Leakage vs. Temperature

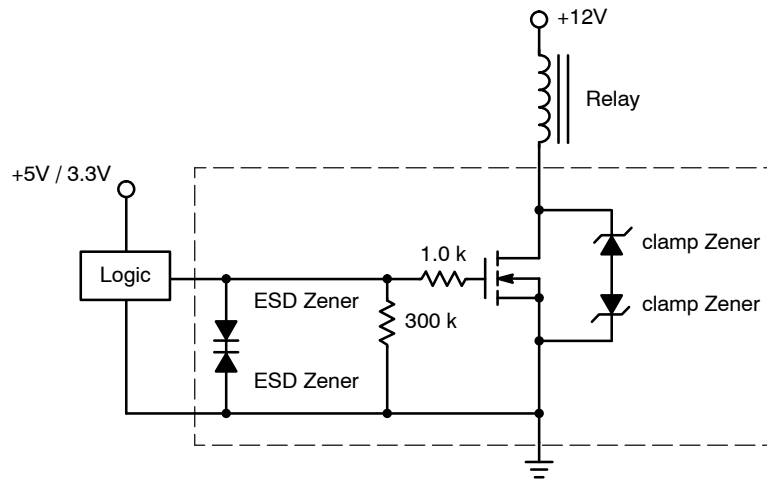


Figure 10. Typical Application Circuit

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

ON Semiconductor®



SOT-23 (TO-236)
CASE 318-08
ISSUE AS

DATE 30 JAN 2018

SCALE 4:1



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	---	10°	0°	---	10°

RECOMMENDED SOLDERING FOOTPRINT



GENERIC MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code
▪ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

- | | | | |
|---|---|---|--|
| STYLE 1 THRU 5:
CANCELLED | STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR | STYLE 7:
PIN 1. EMITTER
2. BASE
3. COLLECTOR | STYLE 8:
PIN 1. ANODE
2. NO CONNECTION
3. CATHODE |
| STYLE 9:
PIN 1. ANODE
2. ANODE
3. CATHODE | STYLE 10:
PIN 1. DRAIN
2. SOURCE
3. GATE | STYLE 11:
PIN 1. ANODE
2. CATHODE
3. CATHODE-ANODE | STYLE 12:
PIN 1. CATHODE
2. CATHODE
3. ANODE |
| STYLE 13:
PIN 1. SOURCE
2. DRAIN
3. GATE | STYLE 14:
PIN 1. CATHODE
2. GATE
3. ANODE | STYLE 15:
PIN 1. GATE
2. CATHODE
3. ANODE | STYLE 16:
PIN 1. ANODE
2. CATHODE
3. CATHODE |
| STYLE 17:
PIN 1. NO CONNECTION
2. ANODE
3. CATHODE | STYLE 18:
PIN 1. NO CONNECTION
2. CATHODE
3. ANODE | STYLE 19:
PIN 1. CATHODE
2. ANODE
3. CATHODE-ANODE | STYLE 20:
PIN 1. CATHODE
2. ANODE
3. GATE |
| STYLE 21:
PIN 1. GATE
2. SOURCE
3. DRAIN | STYLE 22:
PIN 1. RETURN
2. OUTPUT
3. INPUT | STYLE 23:
PIN 1. ANODE
2. ANODE
3. CATHODE | STYLE 24:
PIN 1. GATE
2. DRAIN
3. SOURCE |
| STYLE 25:
PIN 1. ANODE
2. CATHODE
3. GATE | STYLE 26:
PIN 1. CATHODE
2. ANODE
3. NO CONNECTION | STYLE 27:
PIN 1. CATHODE
2. CATHODE
3. CATHODE | STYLE 28:
PIN 1. ANODE
2. ANODE
3. ANODE |

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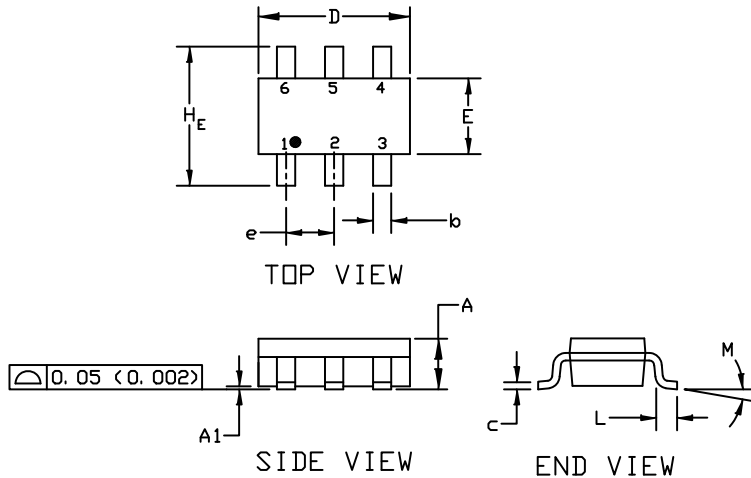
MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



SCALE 2:1

SC-74
CASE 318F
ISSUE P

DATE 07 OCT 2021

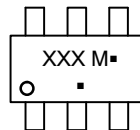


NOTES:

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DIM	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.90	1.00	1.10	0.035	0.039	0.043
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.25	0.37	0.50	0.010	0.015	0.020
c	0.10	0.18	0.26	0.004	0.007	0.010
D	2.90	3.00	3.10	0.114	0.118	0.122
E	1.30	1.50	1.70	0.051	0.059	0.067
e	0.85	0.95	1.05	0.034	0.037	0.041
HE	2.50	2.75	3.00	0.099	0.108	0.118
L	0.20	0.40	0.60	0.008	0.016	0.024
M	0*	---	10*	0*	---	10*

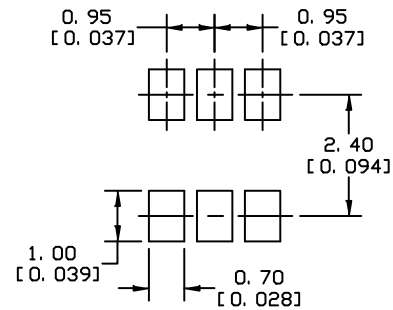
GENERIC MARKING DIAGRAM*



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(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



* For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERM/D.

SOLDERING FOOTPRINT

- | | | | | | |
|---|--|---|--|---|---|
| <p>STYLE 1:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. CATHODE
5. ANODE
6. CATHODE</p> | <p>STYLE 2:
PIN 1. NO CONNECTION
2. COLLECTOR
3. EMITTER
4. NO CONNECTION
5. COLLECTOR
6. BASE</p> | <p>STYLE 3:
PIN 1. EMITTER 1
2. BASE 1
3. COLLECTOR 2
4. EMITTER 2
5. BASE 2
6. COLLECTOR 1</p> | <p>STYLE 4:
PIN 1. COLLECTOR 2
2. EMITTER 1/EMITTER 2
3. COLLECTOR 1
4. EMITTER 3
5. BASE 1/BASE 2/COLLECTOR 3
6. BASE 3</p> | <p>STYLE 5:
PIN 1. CHANNEL 1
2. ANODE
3. CHANNEL 2
4. CHANNEL 3
5. CATHODE
6. CHANNEL 4</p> | <p>STYLE 6:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. CATHODE
5. CATHODE
6. CATHODE</p> |
| <p>STYLE 7:
PIN 1. SOURCE 1
2. GATE 1
3. DRAIN 2
4. SOURCE 2
5. GATE 2
6. DRAIN 1</p> | <p>STYLE 8:
PIN 1. EMITTER 1
2. BASE 2
3. COLLECTOR 2
4. EMITTER 2
5. BASE 1
6. COLLECTOR 1</p> | <p>STYLE 9:
PIN 1. EMITTER 2
2. BASE 2
3. COLLECTOR 1
4. EMITTER 1
5. BASE 1
6. COLLECTOR 2</p> | <p>STYLE 10:
PIN 1. ANODE/CATHODE
2. BASE
3. EMITTER
4. COLLECTOR
5. ANODE
6. CATHODE</p> | <p>STYLE 11:
PIN 1. EMITTER
2. BASE
3. ANODE/CATHODE
4. ANODE
5. CATHODE
6. COLLECTOR</p> | |

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[00-8275-RDNP](#) [00-8722-RDPP](#) [00-8728-WHPP](#) [00-8869-RDPP](#) [00-9051-RDPP](#) [00-9091-LRPP](#) [00-9291-RDPP](#) [0207100000](#) [0207400000](#)
[01312](#) [0134220000](#) [60713816](#) [M15730061](#) [61161-90](#) [61278-0020](#) [6131-204-23149P](#) [6131-205-17149P](#) [6131-209-15149P](#) [6131-218-17149P](#)
[6131-220-21149P](#) [6131-260-2358P](#) [6131-265-11149P](#)